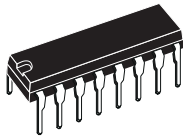
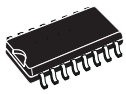
HCF4585B

4-BIT MAGNITUDE COMPARATOR

- EXPANSION TO 8, 12, 16....4 N BITS BY CASCADING UNIT
- MEDIUM SPEED OPERATION : COMPARES TWO 4-BIT WORDS IN 180ns (Typ.) at 10V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



DIP



SOP

ORDER CODES

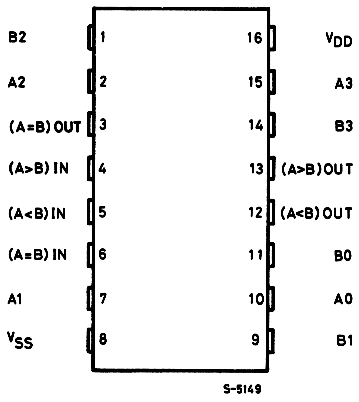
PACKAGE	TUBE	T & R
DIP	HCF4585BEY	
SOP	HCF4585BM1	HCF4585M013TR

DESCRIPTION

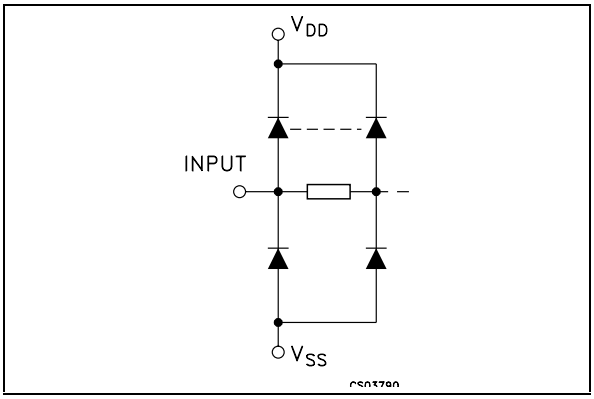
HCF4585B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages.
HCF4585B is a 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to" or "greater than" a second 4-bit word.

HCF4585B has eight comparing inputs (A3, B3 through A0, B0), three outputs (A<B, A=B, A>B) and three cascading inputs (A<B, A=B, A>B) that permit system designers to expand the comparator function to 8, 12, 16...4N bits. When a single HCF4585B is used, the cascading inputs are connected as follows: (A<B) = low, (A=B) = high, (A>B) = high. Cascading these units for comparison of more than 4 bits is accomplished as shown in Typical application.

PIN CONNECTION



IINPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

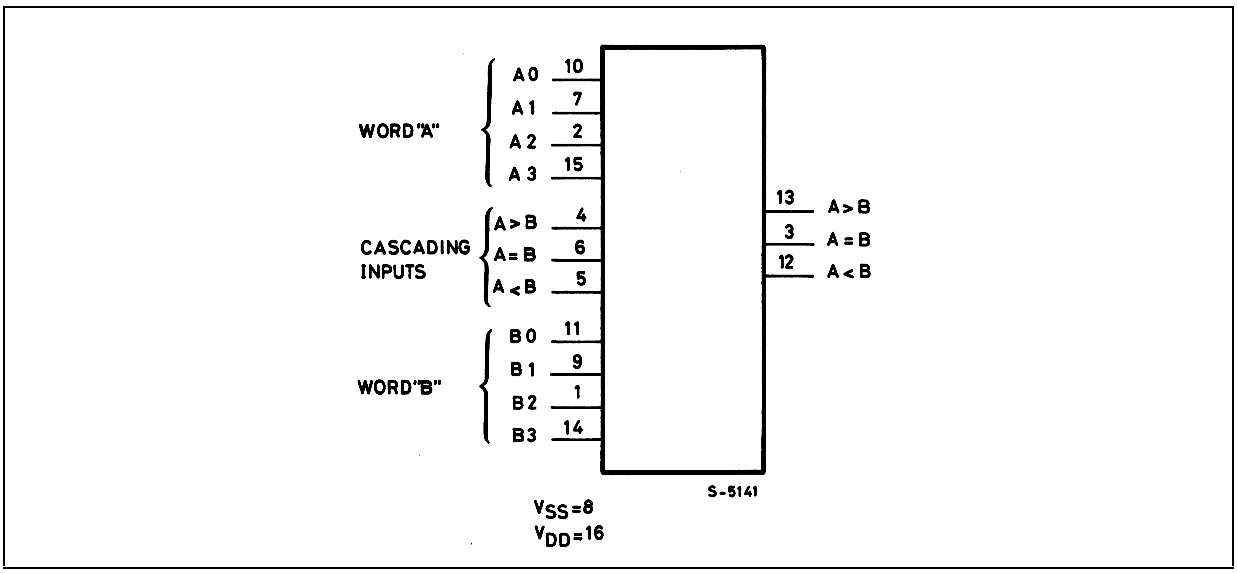
PIN No	SYMBOL	NAME AND FUNCTION
10, 7, 2, 15	A0 to A3	Word A Inputs
11, 9, 1, 14	B0 to B3	Word B Inputs
13, 3, 12	A>B, A=B, A<B	Outputs
4, 6, 5	A>B, A=B, A<B	Cascading Inputs
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

TRUTH TABLE

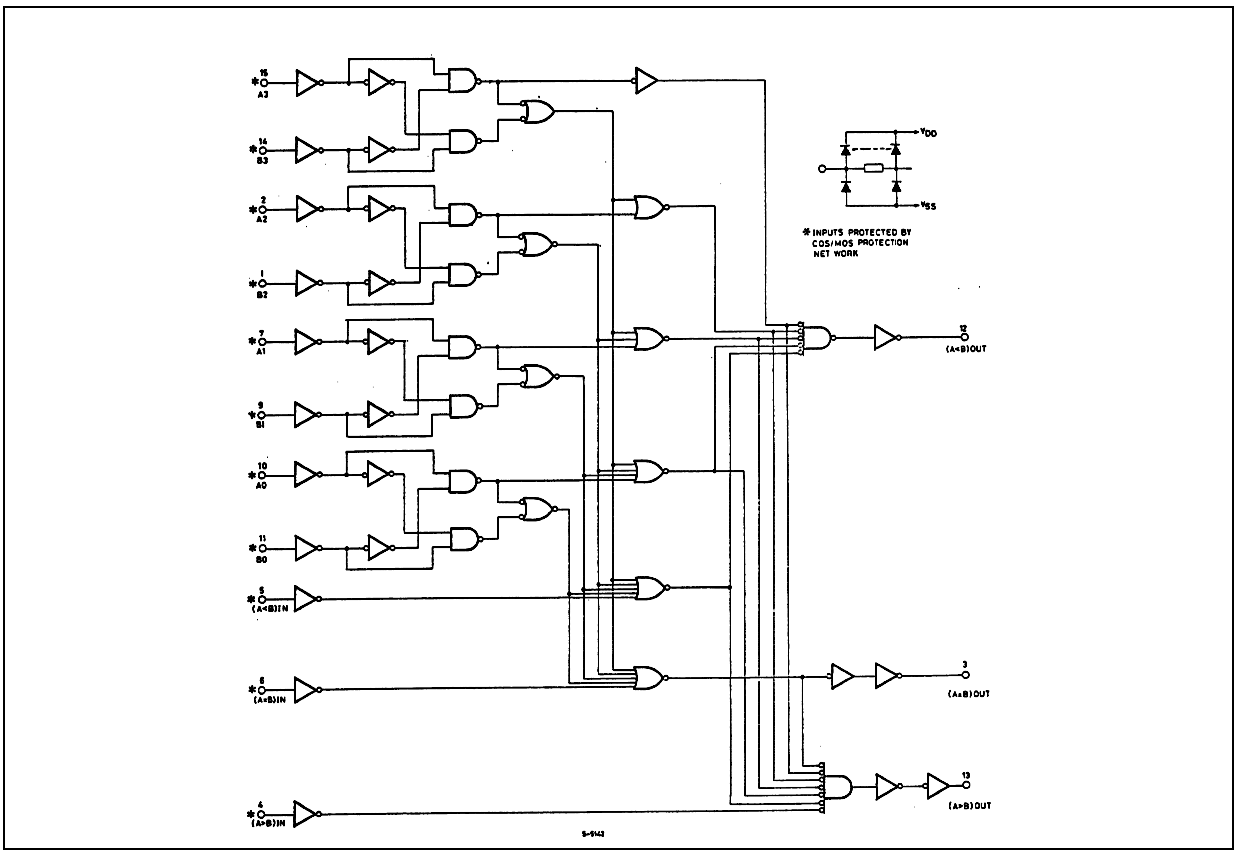
INPUTS							OUTPUTS		
COMPARING				CASCADING					
A3, B3	A2, B2	A1, B1	A0, B0	A<B	A=B	A>B	A<B	A=B	A>B
A3 > B3	X	X	X	X	X	H	L	L	H
A3 = B3	A2 > B2	X	X	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 > B1	X	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	H	X	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	H	L	X	H	L	L
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	H	L	L
A3 = B3	A2 = B2	A1 < B1	X	X	X	X	H	L	L
A3 = B3	A2 < B2	X	X	X	X	X	H	L	L
A3 < B3	X	X	X	X	X	X	H	L	L

X : Don't Care

FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V_I	DC Input Voltage	-0.5 to V_{DD} + 0.5	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.
All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I_L	Quiescent Current	0/5			5		0.04	5		150		150	μA
		0/10			10		0.04	10		300		300	
		0/15			15		0.04	20		600		600	
		0/20			20		0.08	100		3000		3000	
V_{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V_{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I_{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.1		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I_{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I_I	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	±0.1		±1		±1	μA
C_I	Input Capacitance		Any Input				5	7.5					pF

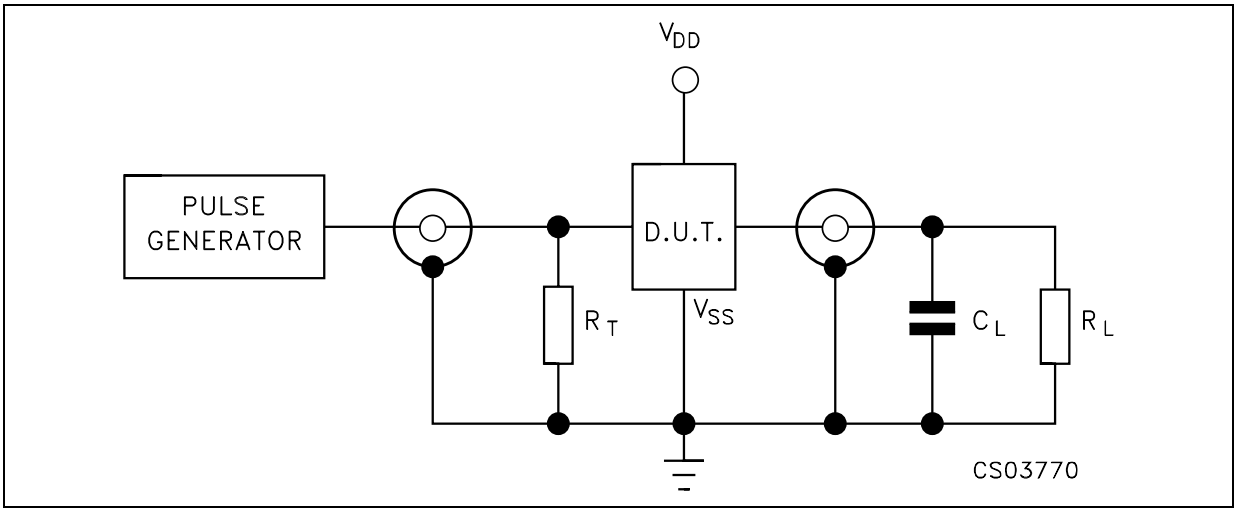
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, $t_r = t_f$ = 20 ns)

Symbol	Parameter	Test Condition		Value (*)			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PHL} t_{PLH}	Propagation Delay Time	5	Comparing Inputs to Outputs		300	600	ns
		10			125	250	
		15			80	160	
t_{PHL} t_{PLH}	Propagation Delay Time	5	Cascading Inputs to Outputs		200	400	ns
		10			80	160	
		15			60	120	
t_{THL} t_{TLH}	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

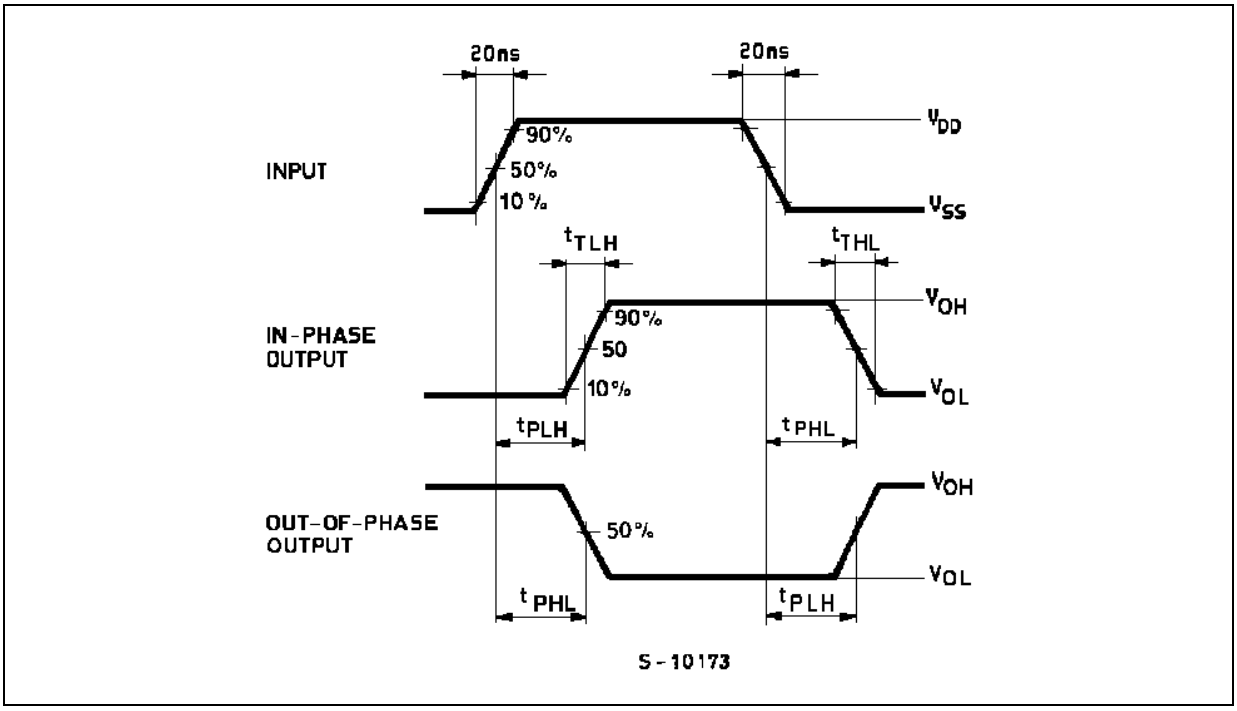
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TEST CIRCUIT



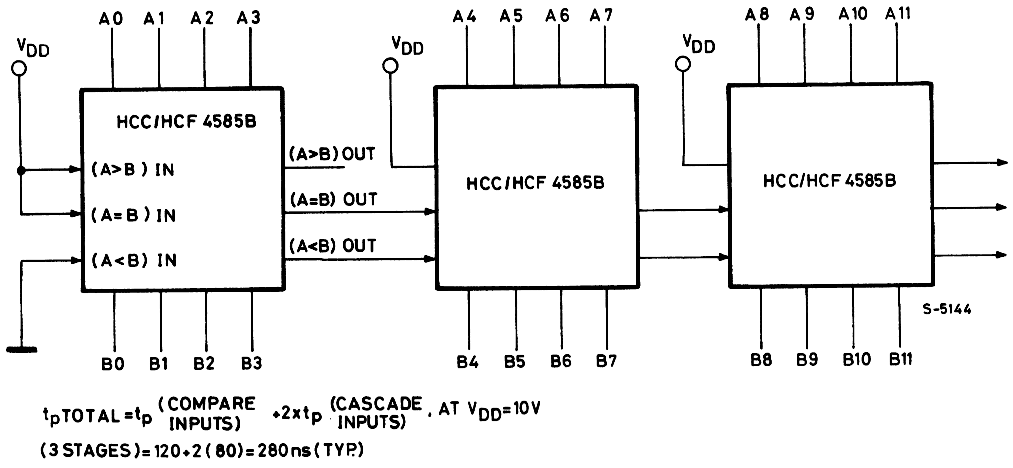
C_L = 50pF or equivalent (includes jig and probe capacitance)
R_L = 200KΩ
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



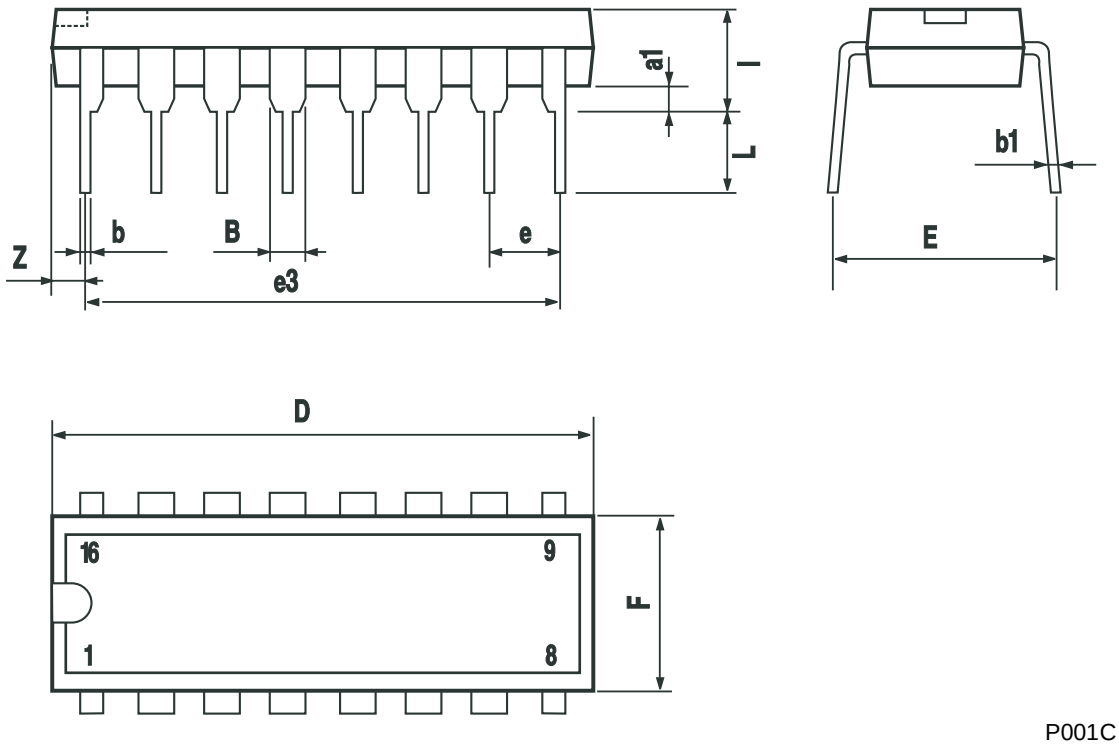
TYPICAL APPLICATION

TYPICAL SPEED CHARACTERISTICS OF A 12-BIT COMPARATOR



Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



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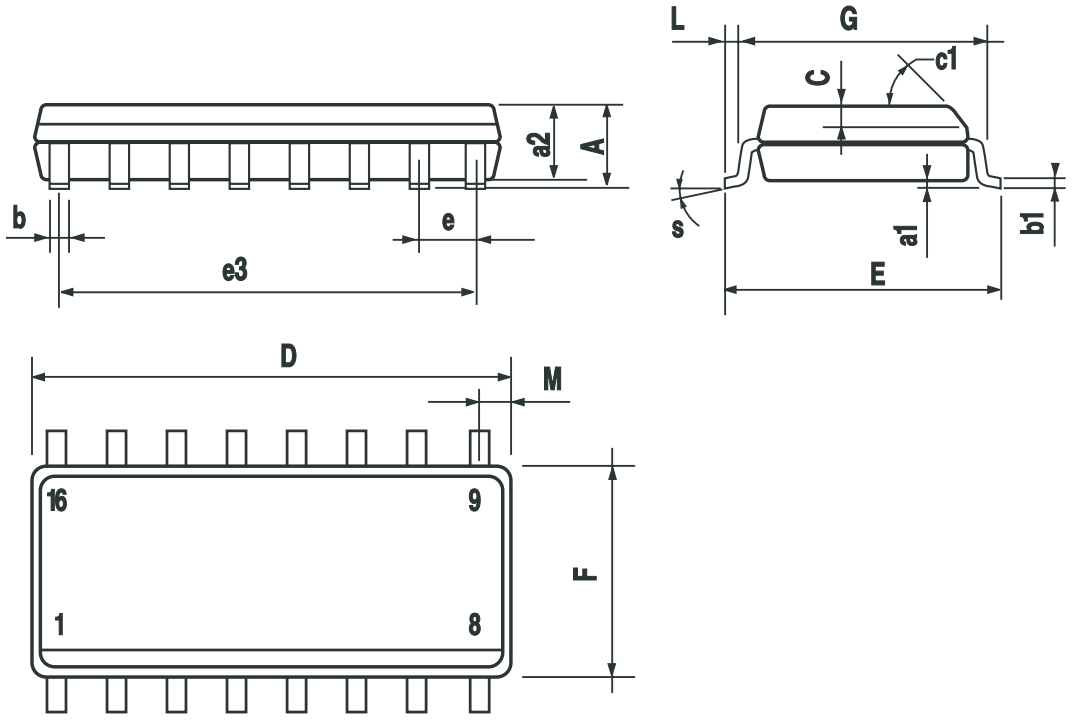
SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



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